promoting crystallinity of the crystallized semiconductor film by irradiation of laser or intense light,

wherein the promoting material comprises one or more elements selected from the group consisting of group 14 elements.

16. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface;

forming a film comprising germanium in contact with said semiconductor film by vapor phase deposition with a germanium compound gas;

heating said semiconductor film with said film comprising germanium to crystallize said semiconductor film[.]; and

removing the film comprising germanium.

19. (Amended) The method according to claim 16 [further comprising a], wherein the step of removing said film comprising germanium is after the heating of [crystallization of] said semiconductor film.

20. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface;

forming a film comprising germanium in contact with said semiconductor film by vapor phase deposition with a germanium compound gas;

heating said semiconductor film with said film comprising germanium to crystallize said semiconductor film;

removing the film comprising germanium;

patterning the crystallized semiconductor film into at least one semiconductor island; and

forming a thin film transistor with said semiconductor island used as at least a channel forming region thereof.

23. (Amended) The method according to claim 20 [further comprising a], wherein the step of removing said film comprising germanium is after the heating [crystallization of] said semiconductor film.

Please add new claims 39-40 as follows:

--39. The method according to claim 5, wherein the step of removing the promoting material for facilitating crystallization is after crystallizing the semiconductor film by a heat treatment.

40. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface;

forming a film comprising germanium in contact with said semiconductor film by vapor phase deposition with a germanium compound gas;

heating said semiconductor film with said film comprising germanium to crystallize said semiconductor film;

removing the film comprising germanium after the heating said semiconductor film; and

irradiating laser or intense light to said semiconductor film after the removing the film comprising germanium.--

REMARKS

At the outset, the Examiner is thanked for her thorough review and consideration of the present application.

The Examiner's non-final Office Action dated August 30, 2000 has been received and its contents carefully noted. Claims 5-9 and 16-38 were pending in the present application. By this amendment, claims 5, 16, 19, 20, and 23 have been amended and claims 39-40 have been added.